


## Insulated Gate Bipolar Transistor (Trench IGBT), 180 A



SOT-227

PRIMARY CHARACTERISTICS	
$V_{CES}$	1200 V
$I_{C(DC)}$	185 A at 90 °C
$V_{CE(on)}$ typical at 100 A, 25 °C	1.55 V
$I_{F(DC)}$	32 A at 90 °C
Speed	8 kHz to 30 kHz
Package	SOT-227
Circuit configuration	Single switch with AP diode

### FEATURES

- 1200 V trench and field stop technology
- Low switching losses
- Positive temperature coefficient
- Easy paralleling
- Square RBSOA
- 10  $\mu$ s short circuit capability
- HEXFRED® antiparallel diodes with ultrasoft reverse recovery
- $T_J$  maximum = 150 °C
- Fully isolated package
- Very low internal inductance ( $\leq$  5 nH typical)
- Industry standard outline
- UL approved file E78996 
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS  
COMPLIANT**

### BENEFITS

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and parallel
- Direct mounting to heatsink
- Plug-in compatible with other SOT-227 packages
- Very low  $V_{CE(on)}$
- Low EMI, requires less snubbing

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	$V_{CES}$		1200	V
Continuous collector current	$I_C^{(1)}$	$T_C = 25\text{ °C}$	281	A
		$T_C = 90\text{ °C}$	185	
Pulsed collector current	$I_{CM}$		390	
Clamped inductive load current	$I_{LM}$		450	
Gate to emitter voltage	$V_{GE}$		$\pm 20$	V
Diode continuous forward current	$I_F$	$T_C = 25\text{ °C}$	51	A
		$T_C = 90\text{ °C}$	32	
Single pulse forward current	$I_{FSM}$	10 ms sine or 6 ms rectangular pulse, $T_J = 25\text{ °C}$	185	
Power dissipation, IGBT	$P_D$	$T_C = 25\text{ °C}$	1087	W
		$T_C = 90\text{ °C}$	522	
Power dissipation, diode	$P_D$	$T_C = 25\text{ °C}$	216	
		$T_C = 90\text{ °C}$	103	
Isolation voltage	$V_{ISOL}$	Any terminal to case, $t = 1\text{ min}$	2500	V

**Note**

(1) Maximum collector current admitted is 100 A, to do not exceed the maximum temperature of terminals



<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{BR(CES)}$	$V_{GE} = 0\text{ V}, I_C = 5.7\text{ mA}$	1200	-	-	V
Collector to emitter voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 100\text{ A}$	-	1.55	2.05	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	1.71	-	
		$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	1.76	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 5.7\text{ mA}$	4.75	5.8	7.0	
		$V_{CE} = V_{GE}, I_C = 5.7\text{ mA}, T_J = 125\text{ }^\circ\text{C}$	-	4.7	-	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 5.7\text{ mA}$ ( $25\text{ }^\circ\text{C}$ to $125\text{ }^\circ\text{C}$ )	-	-11.4	-	mV/ $^\circ\text{C}$
Transfer characteristics	$V_{GE}$	$V_{DS} = 20\text{ V}, I_D = 100\text{ A}$	-	8.5	-	V
Collector to emitter leakage current	$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$	-	0.6	100	$\mu\text{A}$
		$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	0.4	-	mA
		$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	1.6	-	
Forward voltage drop, diode	$V_{FM}$	$I_F = 40\text{ A}, V_{GE} = 0\text{ V}$	-	3.0	3.5	V
		$I_F = 40\text{ A}, V_{GE} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	3.2	-	
		$I_F = 40\text{ A}, V_{GE} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	3.2	-	
Gate to emitter leakage current	$I_{GES}$	$V_{GE} = \pm 20\text{ V}$	-	-	$\pm 220$	nA

<b>SWITCHING CHARACTERISTICS</b> ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Input capacitance	$C_{ies}$	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}, T_J = 25\text{ }^\circ\text{C}$	-	9350	-	pF			
Reverse transfer capacitance	$C_{res}$		-	350	-				
Turn-on switching loss	$E_{on}$	$I_C = 100\text{ A}, V_{CC} = 720\text{ V}, V_{GE} = 15\text{ V}, R_g = 1.0\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C}$	-	4.4	-	mJ			
Turn-off switching loss	$E_{off}$		-	7.3	-				
Total switching loss	$E_{tot}$		-	11.7	-				
Turn-on delay time	$t_{d(on)}$		Energy losses include tail and diode recovery	-	192	-	ns		
Rise time	$t_r$			-	59	-			
Turn-off delay time	$t_{d(off)}$			-	334	-			
Fall time	$t_f$			-	137	-			
Turn-on switching loss	$E_{on}$			$I_C = 100\text{ A}, V_{CC} = 720\text{ V}, V_{GE} = 15\text{ V}, R_g = 1.0\text{ }\Omega, L = 500\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C}$	-	5.7		-	mJ
Turn-off switching loss	$E_{off}$				-	11.6		-	
Total switching loss	$E_{tot}$				-	17.3		-	
Turn-on delay time	$t_{d(on)}$	-	200		-	ns			
Rise time	$t_r$	-	62		-				
Turn-off delay time	$t_{d(off)}$	-	485		-				
Fall time	$t_f$	-	138	-					
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 450\text{ A}, R_g = 1.0\text{ }\Omega, V_{GE} = 15\text{ V to } 0\text{ V}, V_{CC} = 600\text{ V}, V_P = 1200\text{ V}, L = 500\text{ }\mu\text{H}$	Fullsquare						
Diode reverse recovery time	$t_{rr}$	$I_F = 50\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}, V_R = 400\text{ V}$	-	163	-	ns			
Diode peak reverse current	$I_{rr}$		-	10.4	-	A			
Diode recovery charge	$Q_{rr}$		-	851	-	nC			
Diode reverse recovery time	$t_{rr}$	$I_F = 50\text{ A}, dI_F/dt = 200\text{ A}/\mu\text{s}, V_R = 400\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	225	-	ns			
Diode peak reverse current	$I_{rr}$		-	14.9	-	A			
Diode recovery charge	$Q_{rr}$		-	1698	-	nC			
Short circuit safe operating area	SCSOA	$T_J = 150\text{ }^\circ\text{C}, V_{GE} = 15\text{ V to } 0\text{ V}, V_{CC} = 800\text{ V}, V_P = 1200\text{ V}$	10			$\mu\text{s}$			



THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	$T_J, T_{Stg}$		-40	-	150	°C
Junction to case	IGBT	$R_{thJC}$	-	-	0.115	°C/W
	Diode		-	-	0.57	
Case to heatsink	$R_{thCS}$	Flat, greased surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf. in)
		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf. in)
Case style			SOT-227			

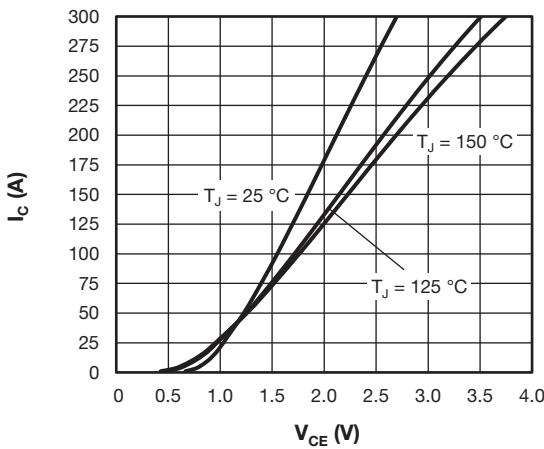


Fig. 1 - Typical IGBT Output Characteristics,  $V_{GE} = 15\text{ V}$

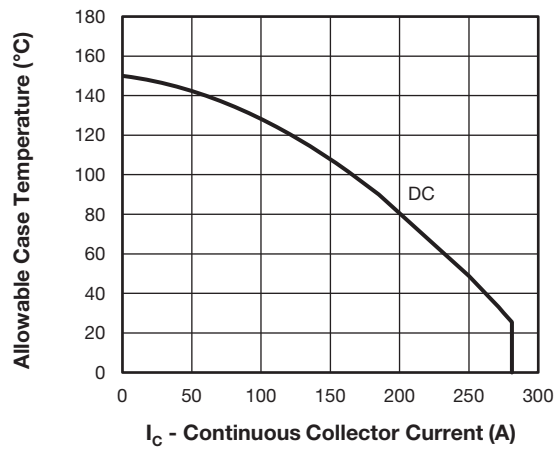


Fig. 3 - Maximum IGBT Continuous Collector Current vs. Case Temperature

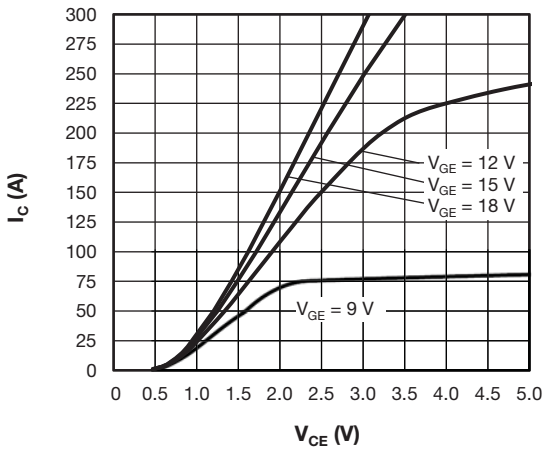


Fig. 2 - Typical IGBT Output Characteristics,  $T_J = 125\text{ °C}$

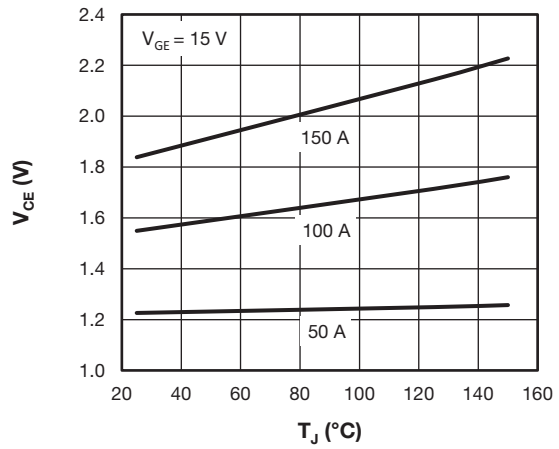


Fig. 4 - Collector to Emitter Voltage vs. Junction Temperature

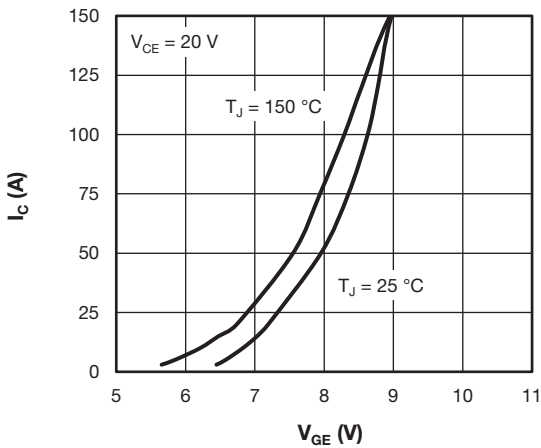


Fig. 5 - Typical IGBT Transfer Characteristics

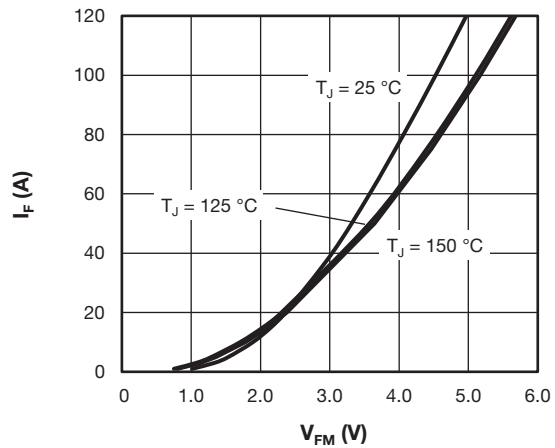


Fig. 8 - Typical Diode Forward Characteristics

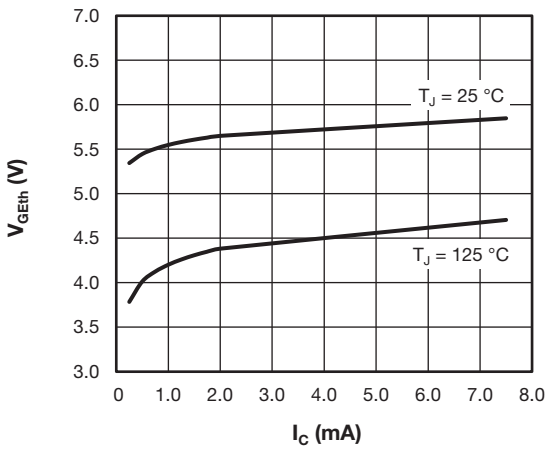


Fig. 6 - Typical IGBT Gate Threshold Voltage

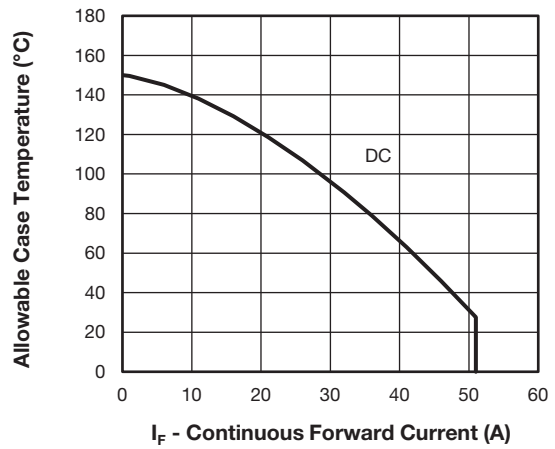


Fig. 9 - Maximum Diode Continuous Forward Current vs. Case Temperature

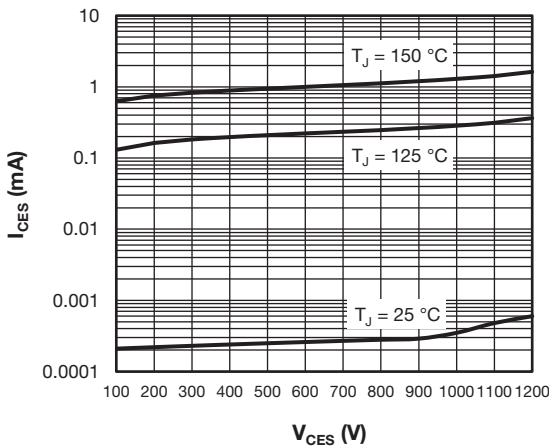


Fig. 7 - Typical IGBT Zero Gate Voltage Collector Current

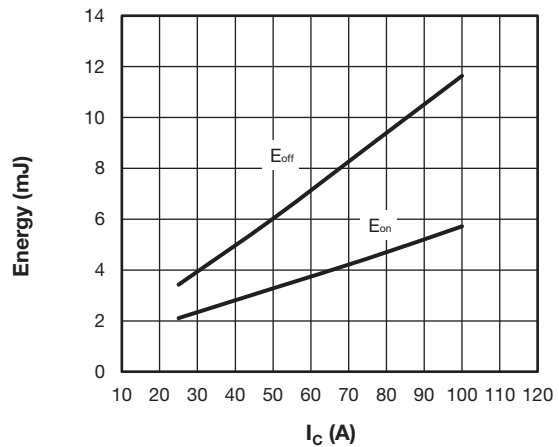


Fig. 10 - Typical IGBT Energy Loss vs.  $I_c$   
 $T_J = 125^\circ\text{C}$ ,  $V_{CC} = 720\text{ V}$ ,  $R_g = 1.0\ \Omega$ ,  $V_{GE} = 15\text{ V}$ ,  $L = 500\ \mu\text{H}$

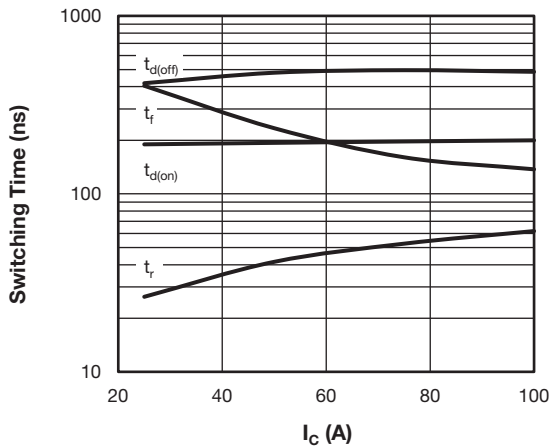


Fig. 11 - Typical IGBT Switching Time vs.  $I_C$   
 $T_J = 125^\circ\text{C}$ ,  $V_{CC} = 720\text{ V}$ ,  $R_g = 1.0\ \Omega$ ,  $V_{GE} = 15\text{ V}$ ,  $L = 500\ \mu\text{H}$

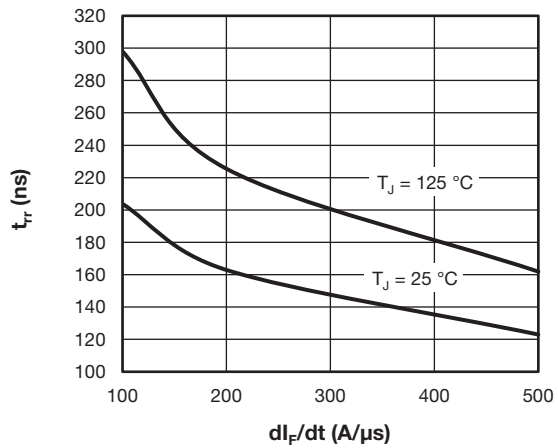


Fig. 14 - Typical Diode Reverse Recovery Time vs.  $di_F/dt$   
 $V_{rr} = 400\text{ V}$ ,  $I_F = 50\text{ A}$

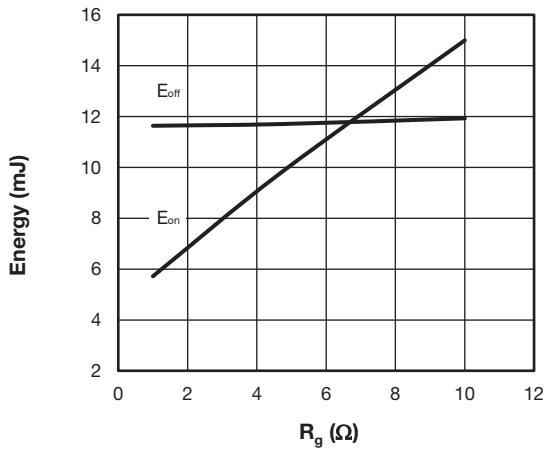


Fig. 12 - Typical IGBT Energy Loss vs.  $R_g$   
 $T_J = 125^\circ\text{C}$ ,  $V_{CC} = 720\text{ V}$ ,  $I_C = 100\text{ A}$ ,  $V_{GE} = 15\text{ V}$ ,  $L = 500\ \mu\text{H}$

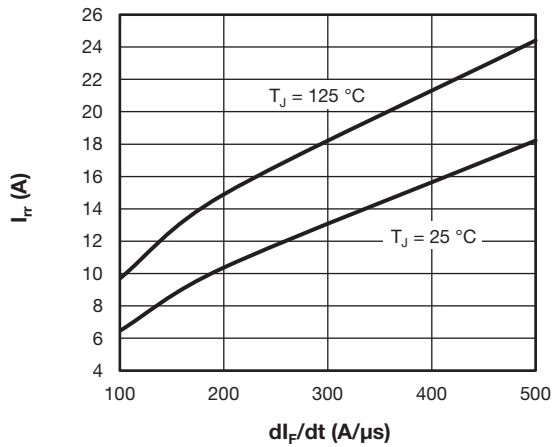


Fig. 15 - Typical Diode Reverse Recovery Current vs.  $di_F/dt$   
 $V_{rr} = 400\text{ V}$ ,  $I_F = 50\text{ A}$

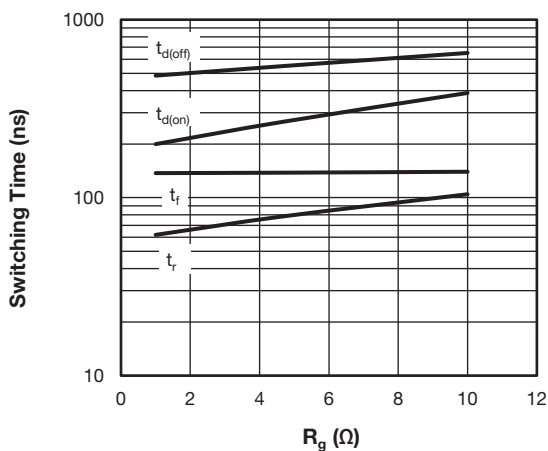


Fig. 13 - Typical IGBT Switching Time vs.  $R_g$   
 $T_J = 125^\circ\text{C}$ ,  $V_{CC} = 720\text{ V}$ ,  $I_C = 100\text{ A}$ ,  $V_{GE} = 15\text{ V}$ ,  $L = 500\ \mu\text{H}$

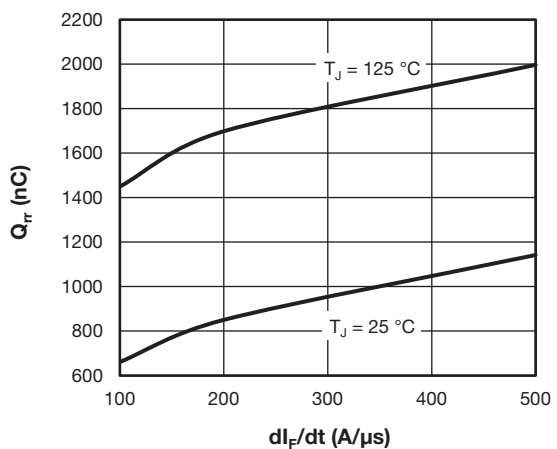


Fig. 16 - Typical Diode Reverse Recovery Charge vs.  $di_F/dt$   
 $V_{rr} = 400\text{ V}$ ,  $I_F = 50\text{ A}$

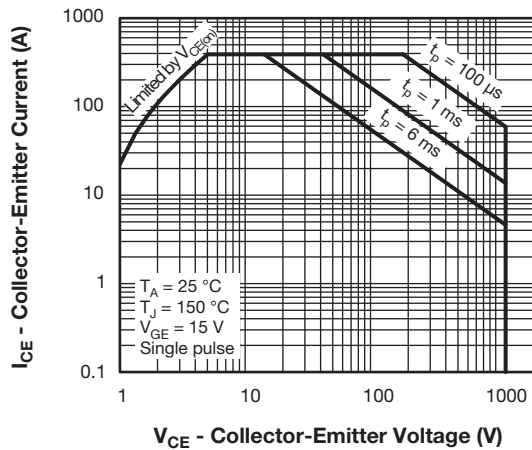


Fig. 17 - IGBT Safe Operating Area

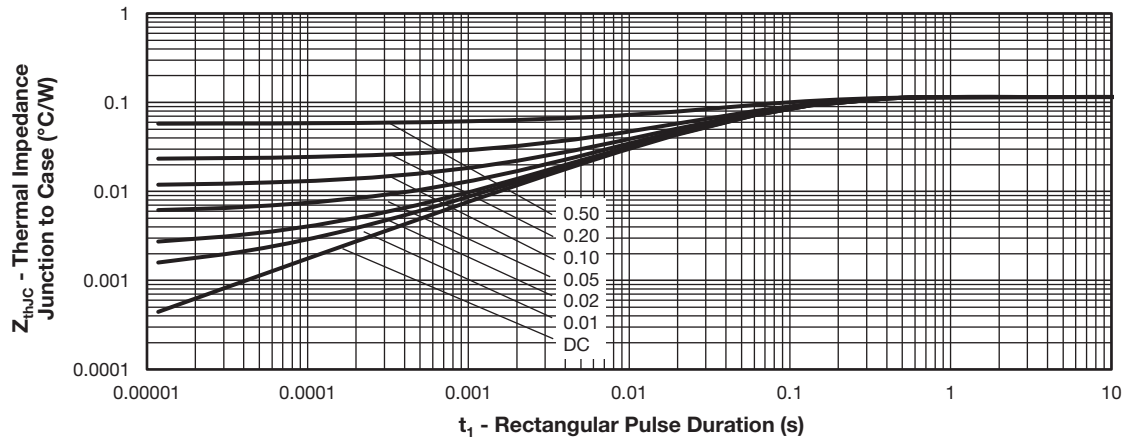


Fig. 18 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics - (IGBT)

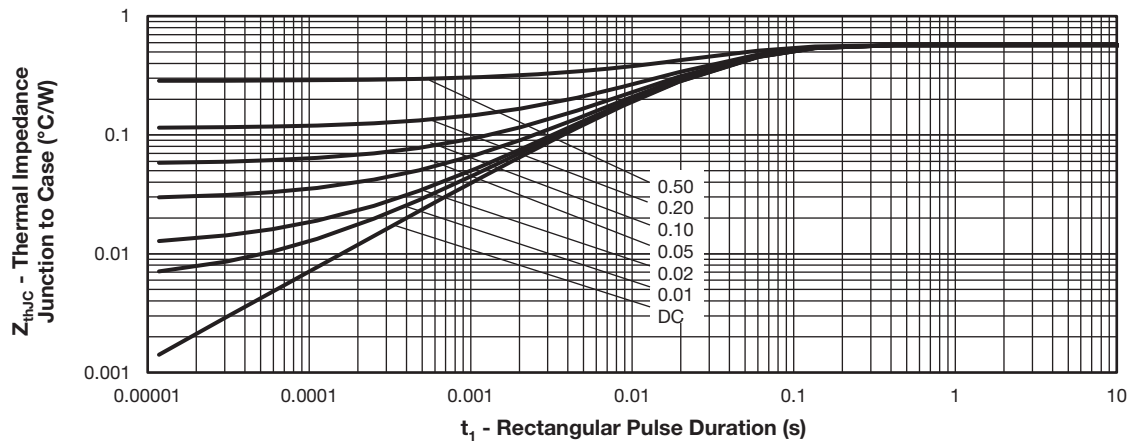


Fig. 19 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics - (Diode)

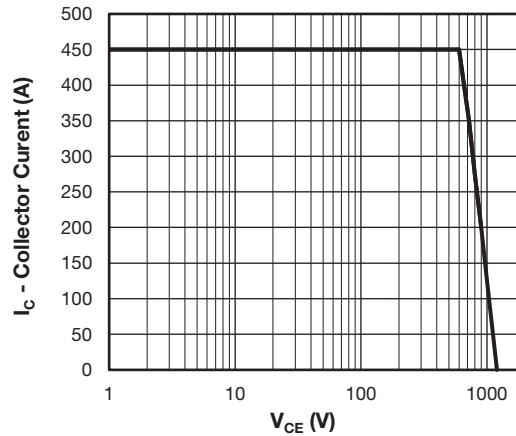


Fig. 20 - IGBT Reverse Bias SOA  
 $V_{GE} = 15 \text{ V}$ ,  $T_J = 150 \text{ }^\circ\text{C}$

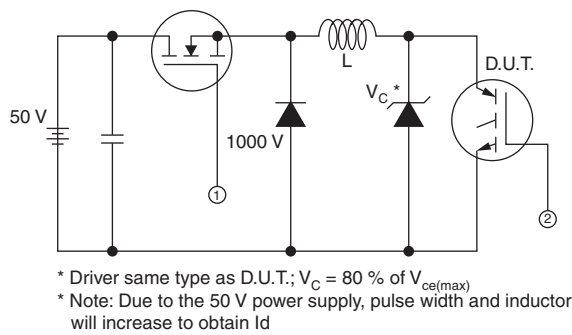


Fig. 21 - Clamped Inductive Load Test Circuit

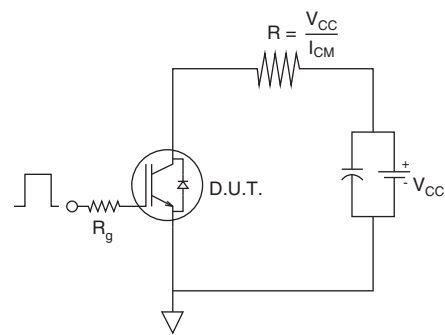


Fig. 22 - Pulsed Collector Current Test Circuit

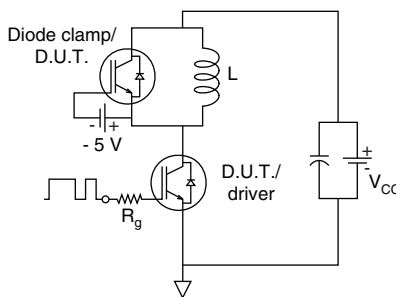


Fig. 23 - Switching Loss Test Circuit

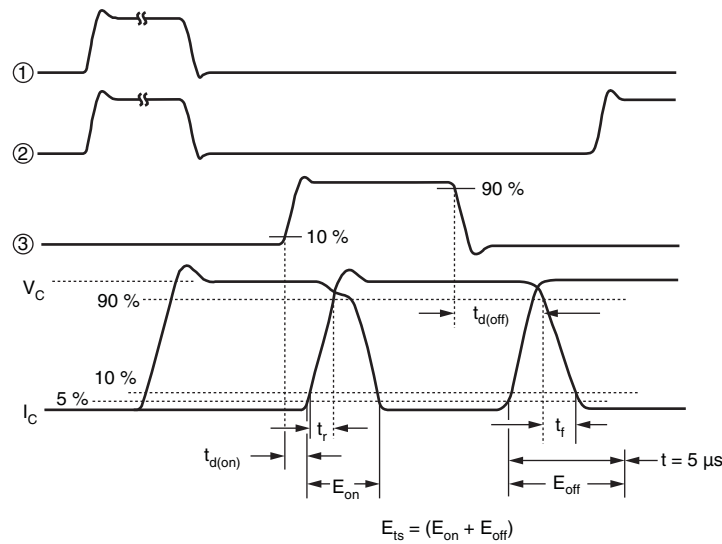


Fig. 24 - Switching Loss Waveforms Test Circuit

**ORDERING INFORMATION TABLE**

Device code	<b>VS-</b>	<b>G</b>	<b>T</b>	<b>180</b>	<b>D</b>	<b>A</b>	<b>120</b>	<b>U</b>
	①	②	③	④	⑤	⑥	⑦	⑧
<b>1</b>	-	Vishay Semiconductors product						
<b>2</b>	-	Insulated gate bipolar transistor (IGBT)						
<b>3</b>	-	Trench IGBT technology						
<b>4</b>	-	Current rating (180 = 180 A)						
<b>5</b>	-	Circuit configuration (D = single switch with antiparallel diode)						
<b>6</b>	-	Package indicator (A = SOT-227)						
<b>7</b>	-	Voltage rating (120 = 1200 V)						
<b>8</b>	-	Speed/type (U = ultrafast)						

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Single switch with AP diode	D	

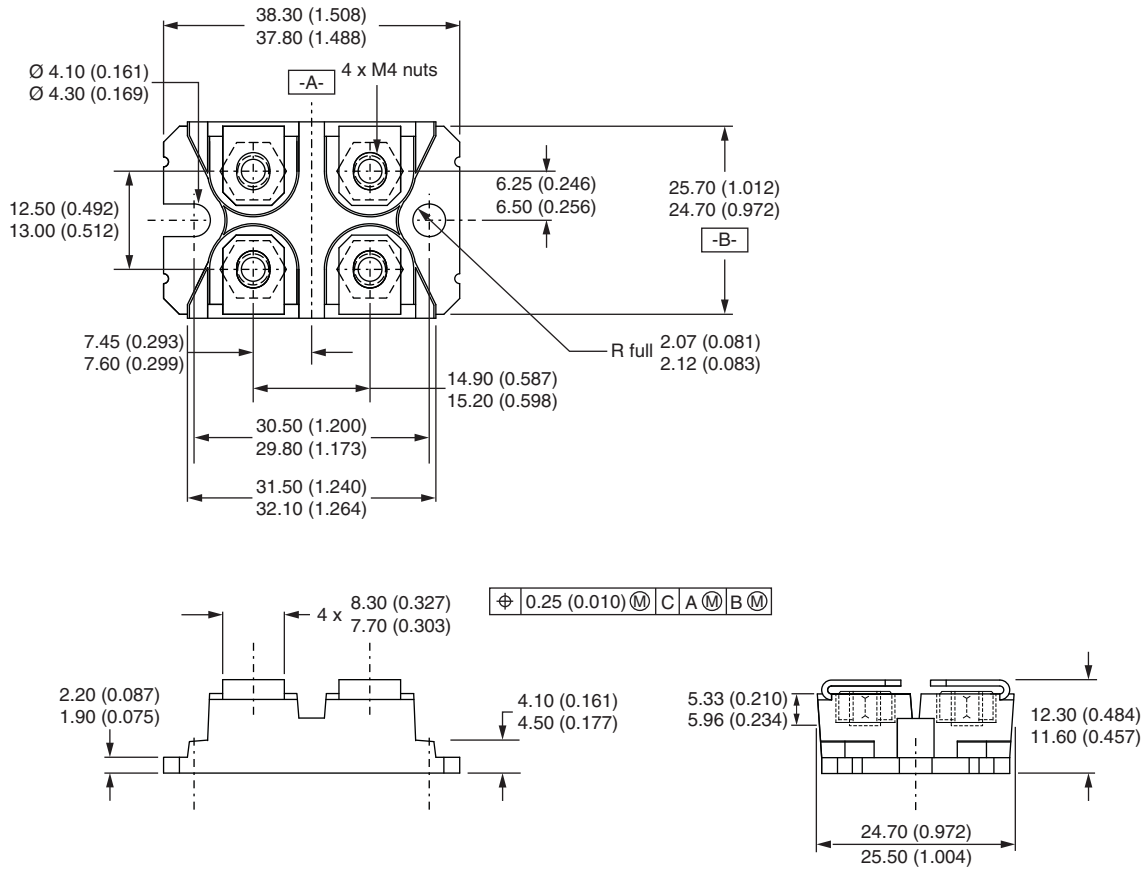
LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95423">www.vishay.com/doc?95423</a>
Packaging information	<a href="http://www.vishay.com/doc?95425">www.vishay.com/doc?95425</a>





### SOT-227 Generation 2

**DIMENSIONS** in millimeters (inches)



**Note**

- Controlling dimension: millimeter



## Disclaimer

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